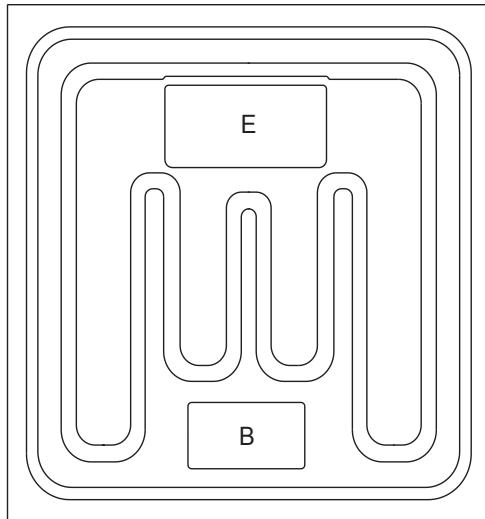


PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	70 x 70 MILS
Die Thickness	9.0 MILS
Base Bonding Pad Area	11.4 x 18 MILS
Emitter Bonding Pad Area	13.7 x 23.6 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Ti / Ni / Ag 11,300Å

GEOMETRY



BACKSIDE COLLECTOR

R1

GROSS DIE PER 4 INCH WAFER

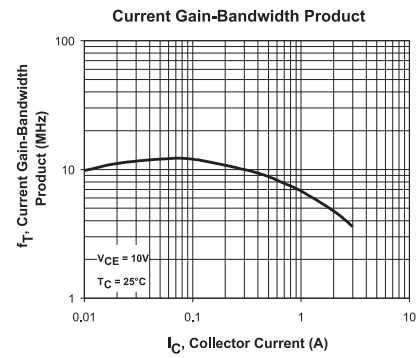
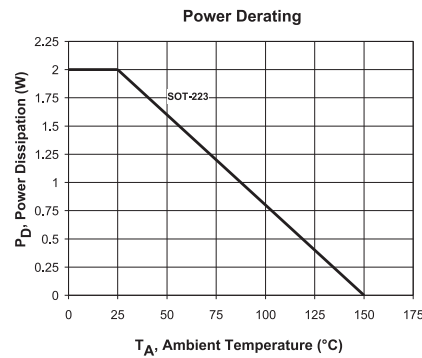
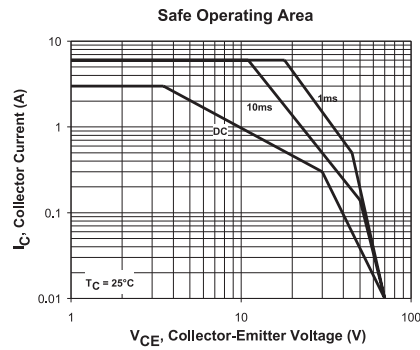
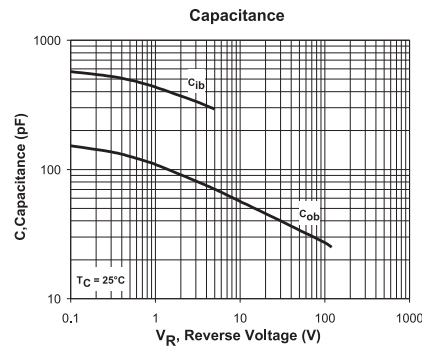
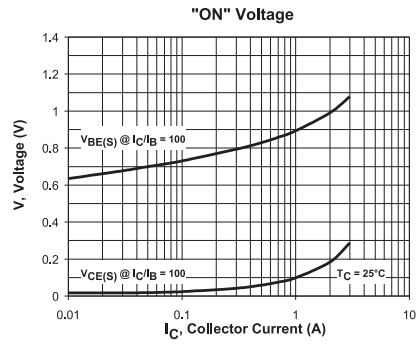
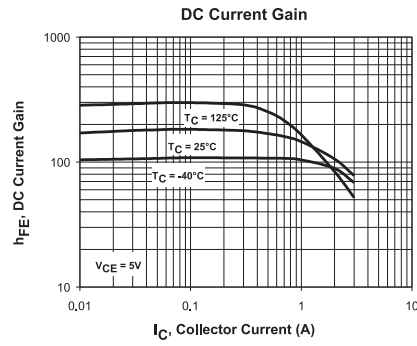
2,200

PRINCIPAL DEVICE TYPES

CZT3120

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R3 (26-March 2004)



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